L Number	Hits	Search Text	DB	Time stamp
1	7	(("5976769") or ("5106786") or ("4820611") or ("5705321") or ("5625220") or ("6010829") or ("5968712")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:33
2	8	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same ($1ARC or antireflect$3 or anti adj reflect$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:35
3	8	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (hardmask or hard adj mask) same ($1ARC or antireflect$3 or anti adj reflect$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:42
4	0	430/331.ccls. and (liquid near3 isotropic$4 same (developer or solution or solvent or etch$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:43
5	153	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (expos$3 or pattern$3 or radiat$3 or irradiat$3) same (resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (x adj ray or extreme adj ultraviolet or EUV or extreme adj UV or "157" adj nm or "193" adj nm or deep adj ultraviolet or deep adj UV or DUV or i adj line or particle adj beam or ion adj beam or electron adj beam or e adj beam) not ((((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same ($1ARC or antireflect$3 or anti adj reflect$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:44
6	5	430/331.ccls. and (isotropic$4 same (developer or solution or solvent or etch$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:44

7	1	((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid or wet or solvent or solution) and isotropic$4 near3 etch$3)) and liquid adj isotropic adj etch$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:46
8	45	((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same develop$4 same (tetramethylammonium adj hydroxide or tetramethyl adj ammonium adj hydroxide or TMAH)) and (weak or mild) near3 develop$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:50
9	35	(bak$3 or heat$3) same (resist or photoresist) same (glass adj transition adj temperature or "T.sub.g") same (novolac or novolak or $6hydroxystyrene)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:51
—	1	("5976769").PN.	USPAT; US-PGPUB	2003/08/14 14:16
—	1154	(resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/15 14:36
—	610	((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (semiconduct$3 or optic$4 or mask or photomask or reticle).ti,ab.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/14 16:40
—	279	((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/14 18:25
—	8	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same ($1ARC or antireflect$3 or anti adj reflect$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:34

—	151	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (bak$3 or heat$3) same (resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) not ((((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same ($1ARC or	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/15 14:13
—	5	antireflect$3photoressiadjoreflecg$3adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (hardmask or hard adj mask) same ($1ARC or antireflect$3 or anti adj reflect$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:41
—	1	"5472829".PN.	USPAT; US-PGPUB	2003/08/14 19:58
—	1	"5139904".PN.	USPAT; US-PGPUB	2003/08/15 11:14
—	1	"5324676".PN.	USPAT; US-PGPUB	2003/08/15 11:26
—	1	"5431770".PN.	USPAT; US-PGPUB	2003/08/15 11:27
—	1	"5804088".PN.	USPAT; US-PGPUB	2003/08/15 11:30
—	1	"5885887".PN.	USPAT; US-PGPUB	2003/08/15 11:58
—	1	"5930634".PN.	USPAT; US-PGPUB	2003/08/15 12:01
—	1	"5965461".PN.	USPAT; US-PGPUB	2003/08/15 12:02
—	1	"6020111".PN.	USPAT; US-PGPUB	2003/08/15 12:14
—	1	"6121123".PN.	USPAT; US-PGPUB	2003/08/15 12:54
—	1	"6121123".PN.	USPAT; US-PGPUB	2003/08/15 13:03
—	1	"6156485".PN.	USPAT; US-PGPUB	2003/08/15 13:04
—	1	"6194323".PN.	USPAT; US-PGPUB	2003/08/15 13:12
—	1	"6277750".PN.	USPAT; US-PGPUB	2003/08/15 13:15
—	1	"6281130".PN.	USPAT; US-PGPUB	2003/08/15 13:15
—	0	430/331.ccls. and (liquid near3 isotropic$4 same (developer or solution or solvent or etch$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:43

–	138	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (expos$3 or pattern$3 or radiat$3 or irradiat$3) same (resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (x adj ray or extreme adj ultraviolet or EUV or extreme adj UV or "157" adj nm or "193" adj nm or deep adj ultraviolet or deep adj UV or DUV or i adj line or particle adj beam or ion adj beam or electron adj beam or e adj beam) not ((((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same ($1ARC or antireflect$3 or anti adj reflect$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:43
–	5	430/331.ccls. and (isotropic$4 same (developer or solution or solvent or etch$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:44
–	622	(((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and ((liquid or wet or solvent or solution or isotropic$4) near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (expos$3 or pattern$3 or radiat$3 or irradiat$3) same (resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (x adj ray or extreme adj ultraviolet or EUV or extreme adj UV or "157" adj nm or "193" adj nm or deep adj ultraviolet or deep adj UV or DUV or i adj line or particle adj beam or ion adj beam or electron adj beam or e adj beam) not ((((resist or photoresist or energy adj sensit$4 or photosensit$4 or photo adj sensit$4) same (develop$4 and (reduc$3 or shrink$3 or decreas$3 or less$5 or slim$4 or trim$4) and (liquid near3 etch$3 or isotropic$4 near3 etch$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same ($1ARC or antireflect$3 or anti adj reflect$3))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/15 14:44

–	1	((resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid or wet or solvent or solution) and isotropic\$4 near3 etch\$3)) and liquid adj isotropic adj etch\$3	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:46
–	617	(resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid or wet or solvent or solution) and isotropic\$4 near3 etch\$3)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/15 14:48
–	2783	(resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same develop\$4 same (tetramethylammonium adj hydroxide or tetramethyl adj ammonium adj hydroxide or TMAH)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/08/16 10:53
–	41	((resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same develop\$4 same (tetramethylammonium adj hydroxide or tetramethyl adj ammonium adj hydroxide or TMAH)) and (weak or mild) near3 develop\$4	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:50
–	1	("2000112146").PN.	DERWENT	2003/08/16 13:10
–	0	("10-285215").PN.	DERWENT	2003/08/16 13:10
–	1	("10285215").PN.	DERWENT	2003/08/16 13:10
–	29	(bak\$3 or heat\$3) same (resist or photoresist) same (glass adj transition adj temperature or "T.sub.g") same (novolac or novolak or \$6hydroxystyrene)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11:50